

TUPB108

Genesis of topography in buffered chemical polishing of niobium for application to superconducting radiofrequency accelerator cavities

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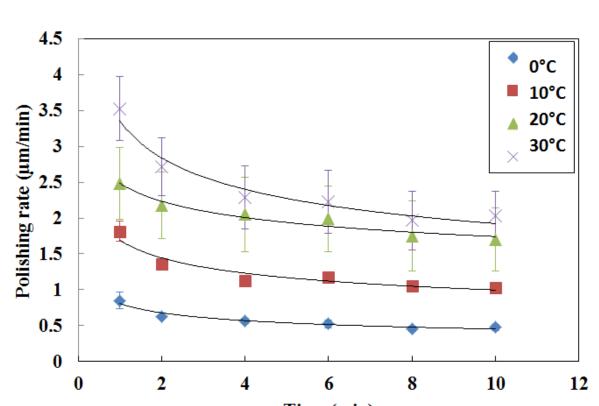
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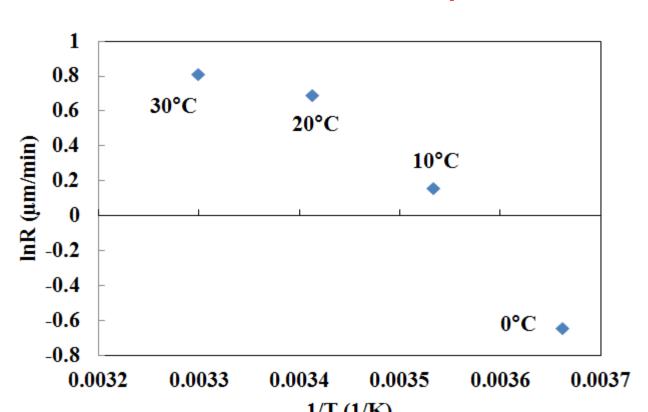
Topography arising from the final etch step in preparing niobium superconducting radiofrequency (SRF) accelerator cavities is understood to significantly impact cavity performance at high field levels. This study investigated the effect of process temperature and time on the etch rate and topography arising from the widely-used buffered chemical polishing (BCP). This study aims to understand more thoroughly the genesis of topography in BCP of polycrystalline niobium. It was found that the etch process is controlled by the surface reaction; and that the etch rate varies with crystallographic orientation. The familiar micron-scale roughening necessarily results. Gas evolution has an impact, but is secondary. The major outcome is that surface smoothness comparable to EP appears to be inherently unachievable for polycrystalline niobium using BCP, setting an upper limit to the gradient for which it is useful.

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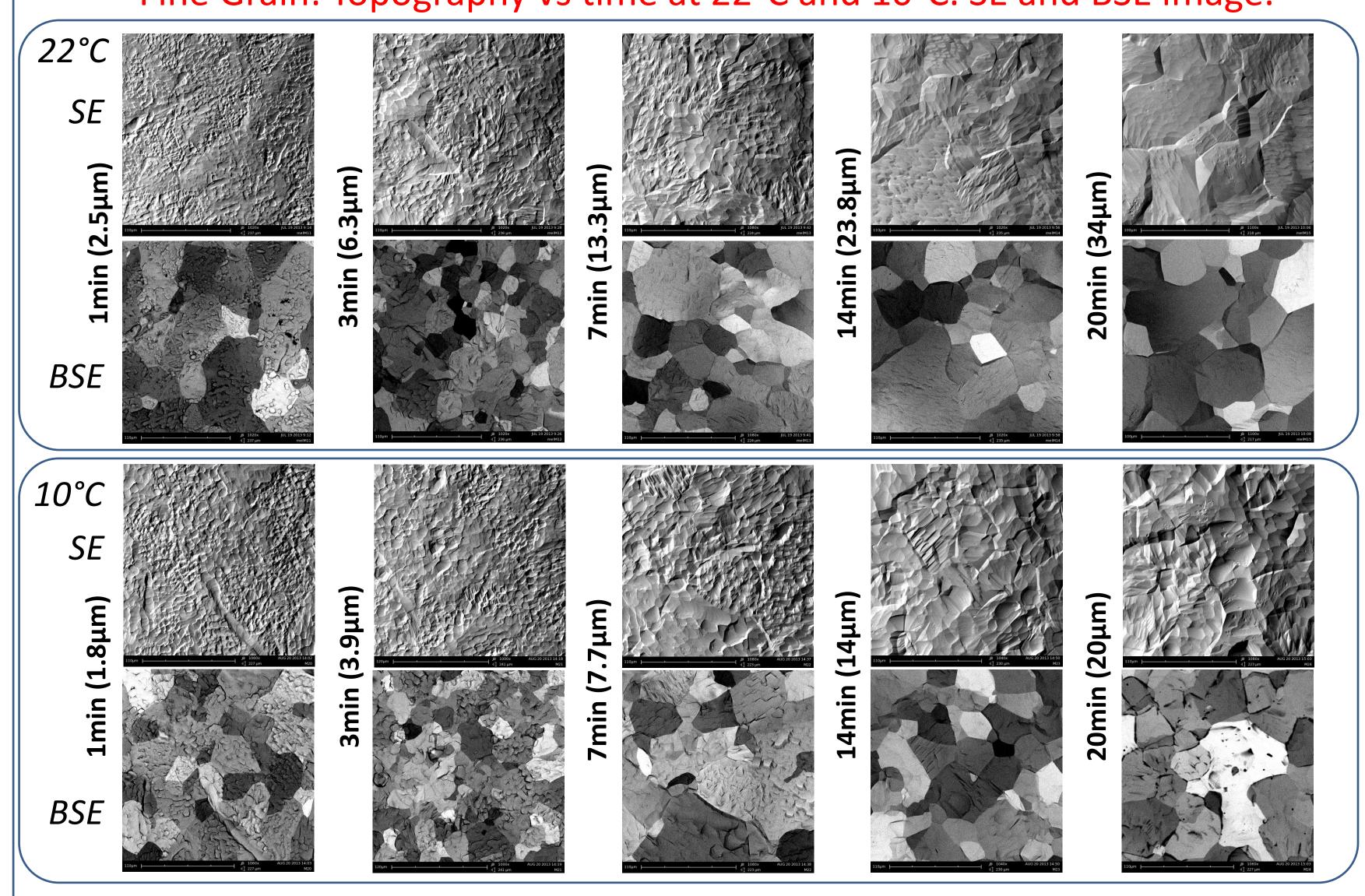
Experiments	Temperature	Duration	Orientation
Fine grain	0-30 °C	1-20 min	Face up/down/sideway
Bi-crystal	RT	12 min	Face up
Single crystal	RT	accu. 90min	Face up

Fine Grain: Static polishing rate vs. time at various temperatures

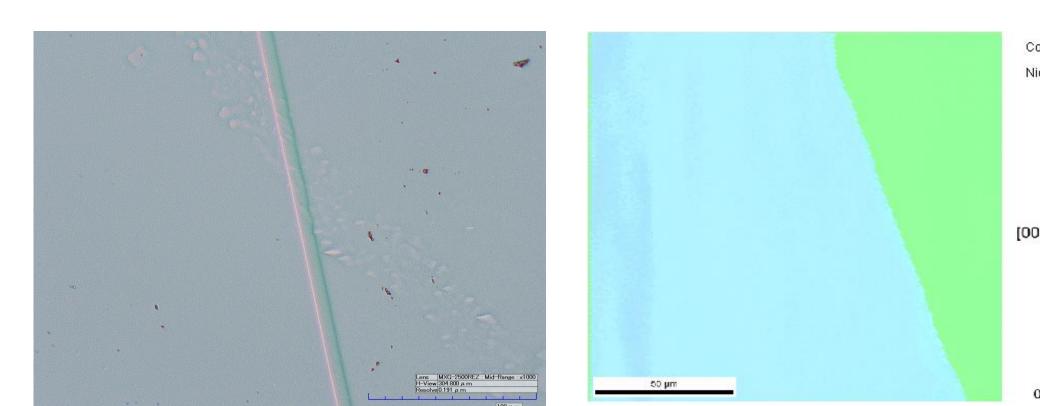


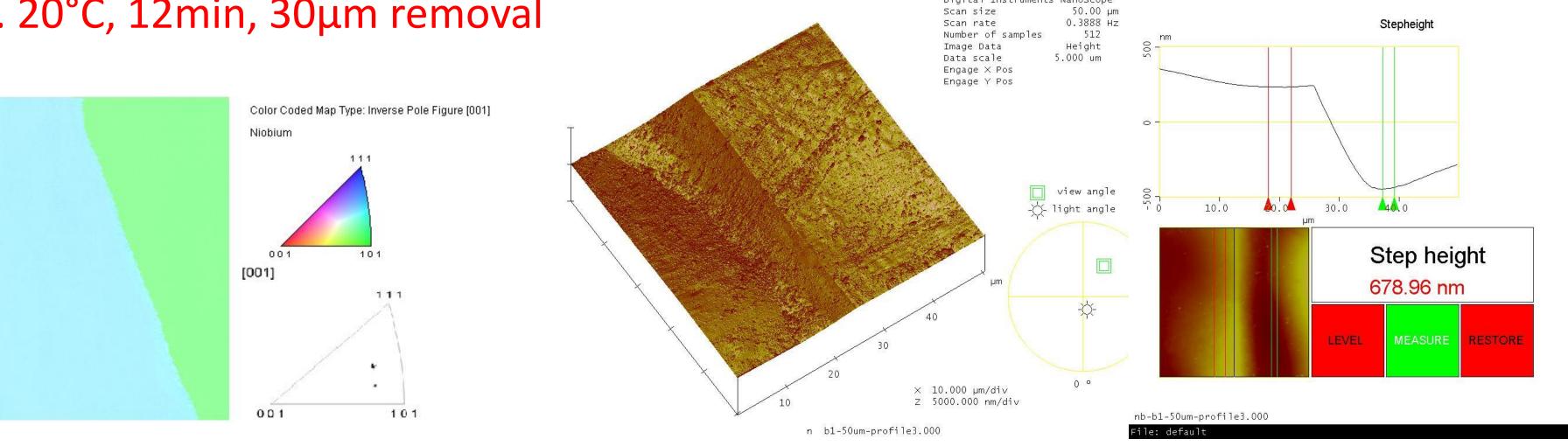


Fine Grain: Topography vs time at 22°C and 10°C. SE and BSE image.

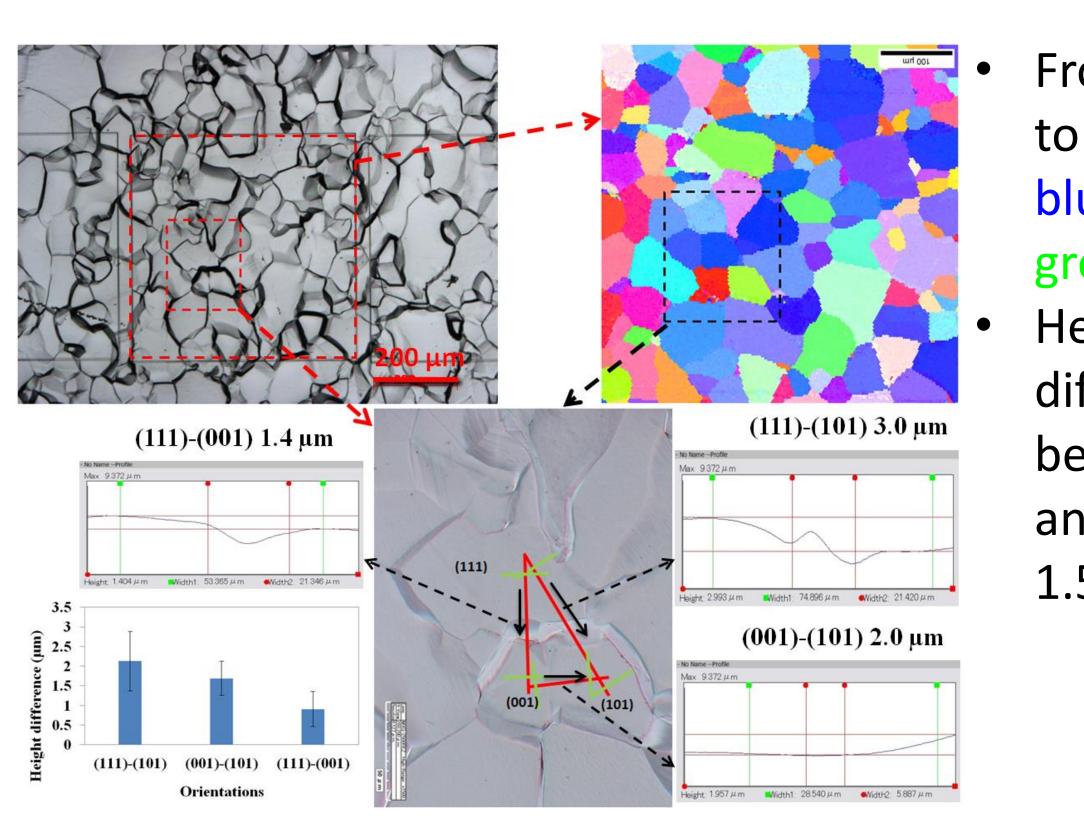


Bi-crystal: Topography, EBSD, AFM. 20°C, 12min, 30µm removal





FG: Topography, EBSD. Nano-polished, RT, 6min, 15µm removal

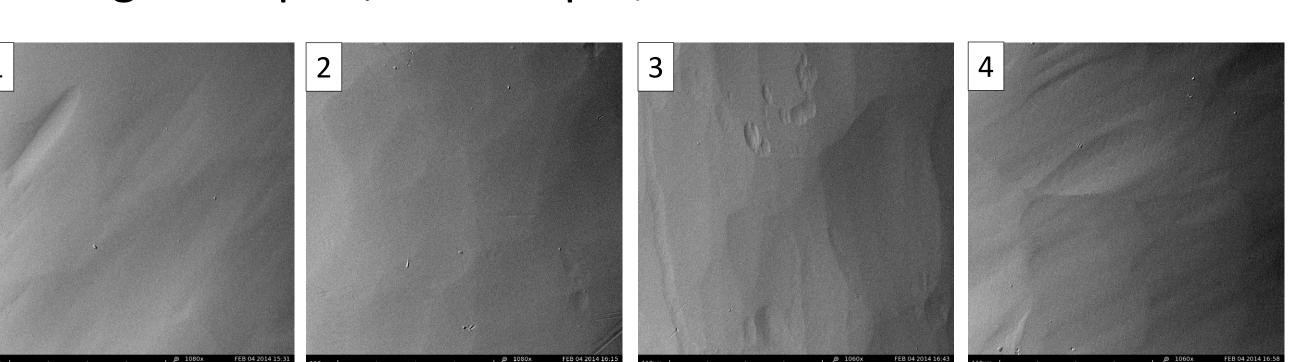


to lowest: blue, red, green

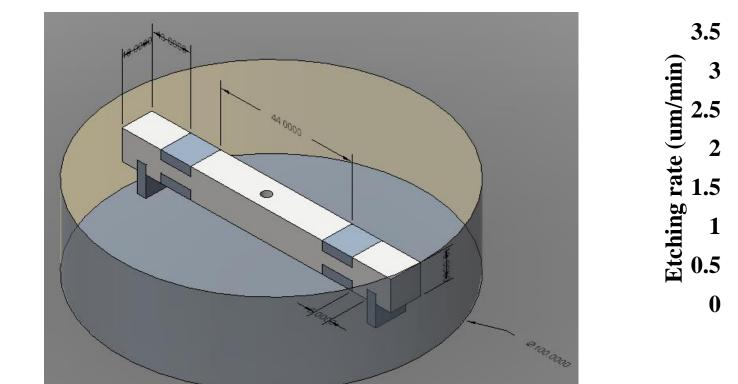
Height difference between blue and green: $1.5-3 \mu m$

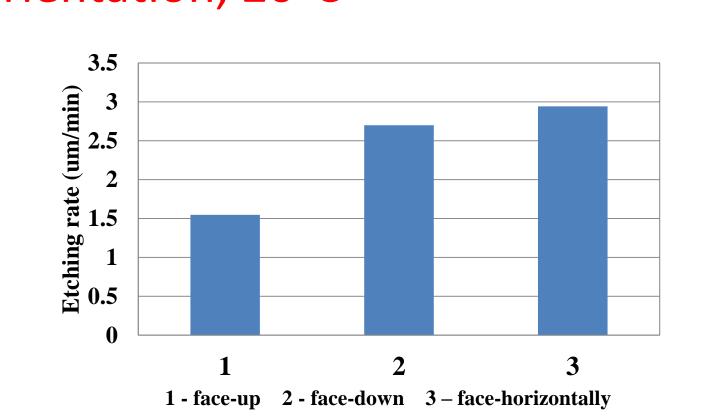
Single crystal: Topography 22°C, 90min, 225μm removal

No significant difference in removal rate among 4 samples, 1.8±0.2 μm/min.

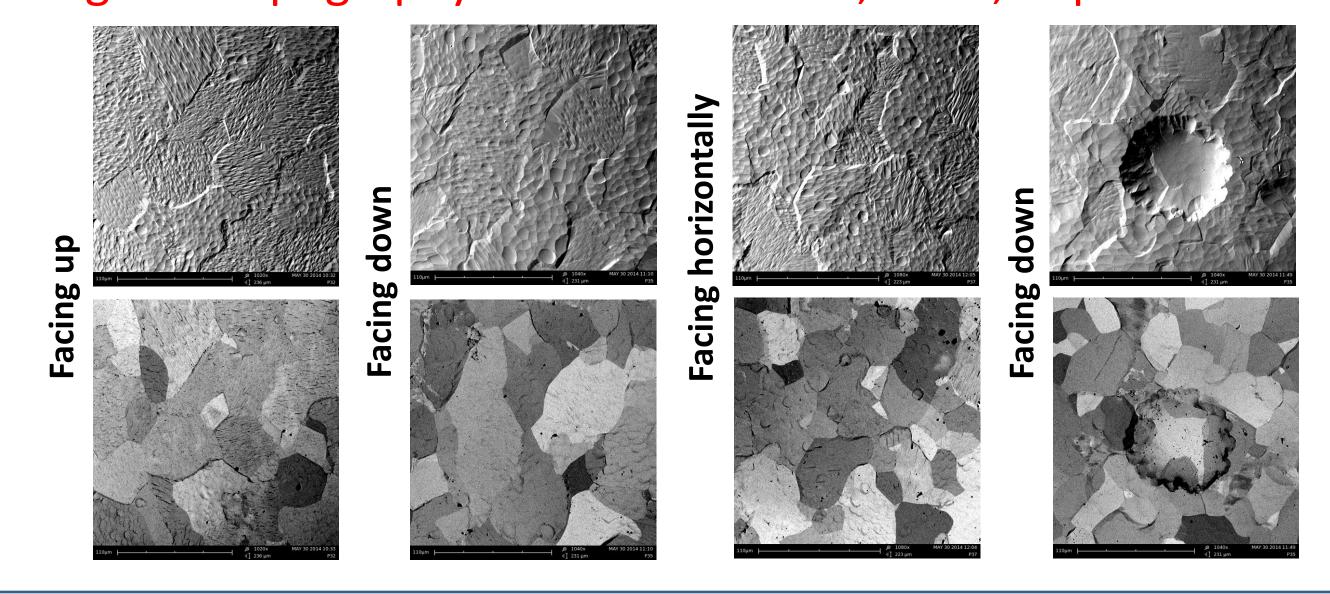


Fine grain: Polishing rate vs orientation, 20°C

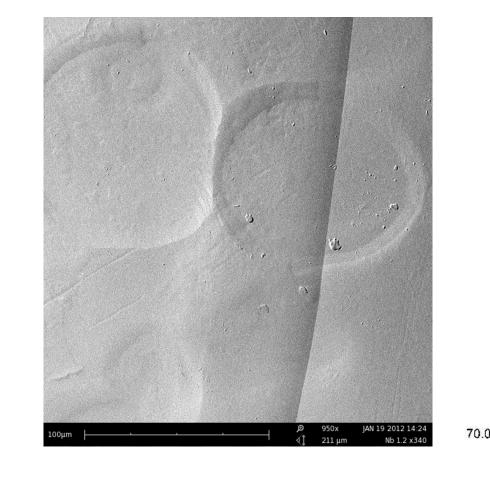


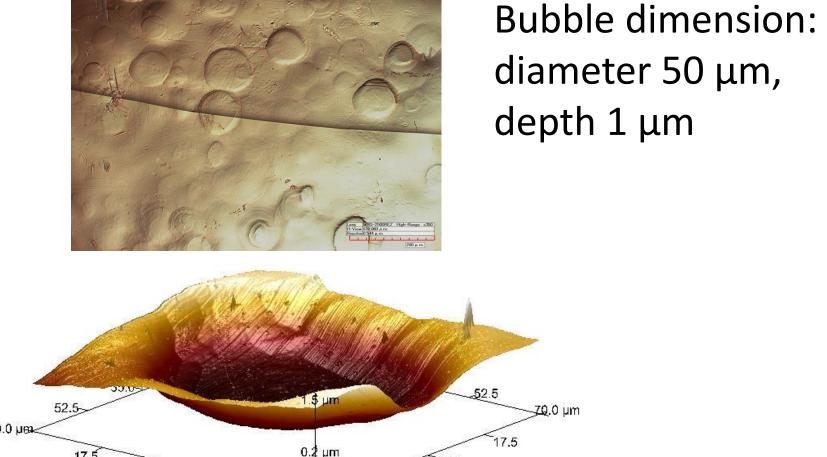


Fine grain: Topography vs orientation. RT, 6min, 15µm removal



Bi-crystal topography: Bubble print. Facing-up, RT, 80 μm removal





- Under static conditions, the topography of BCP'd fine grain niobium is primarily determined by grain orientation dependent differential etching. Step size at grain boundaries depends on the crystal orientation of the two grains. Bubble print from gas evolution is a secondary contributor.
- Polishing rate is temperature and sample orientation dependent.
- Topography is decided by total removal, which is a combined result of time, temperature and orientation.

Acknowledgement:

Work supported by Office of High Energy Physics, U.S. Department of Energy, Grant SC0007907 to the College of William & Mary and by U.S. DOE Contract No. DE-AC05-06OR23177 to Jefferson Science Associates. Thanks to the College of William and Mary characterization lab for generous help and SEM, AFM, and optical microscope equipment support. Peter Kneisel for the large grain material; Josh Spradlin and Jay Tuggle for EBSD; Tina Wang, Taina Matos, and Melissa Meyerson for characterization efforts; Gary Slack for helping with sample holder.